

- GENERAL PURPOSE SILICON DIODES
- METALLURGICALLY BONDED

CDLL483B
CDLL485B
CDLL486B

MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C
 Storage Temperature: -65°C to +175°C
 Operating Current: 200 mA
 Derating: 1.2mA/°C from 25°C to 150°C
 1.0mA/°C from 150°C to 175°C
 Forward Current: 650mA

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V _{RM}	V _{RWM}	I _O	I _O T _A = +150°C	I _{FSM} T _P = 1/120 S T _A = 25°C
	V(pk)	V(pk)	mA	mA	A
CDLL483B	80	70	200	50	2
CDLL485B	180	180	200	50	2
CDLL486B	250	225	200	50	2

TYPE	V _F @100mA	I _{R1} at V _{RWM} T _A = 25°C	I _{R2} at V _{RWM} T _A = 25°C	I _{R3} at V _{RWM} T _A = 150°C
	V dc	nA dc	μA	μA dc
CDLL483B	0.8 - 1.0	25	100	5
CDLL485B	0.8 - 1.0	25	100	5
CDLL486B	0.8 - 1.0	25	100	5

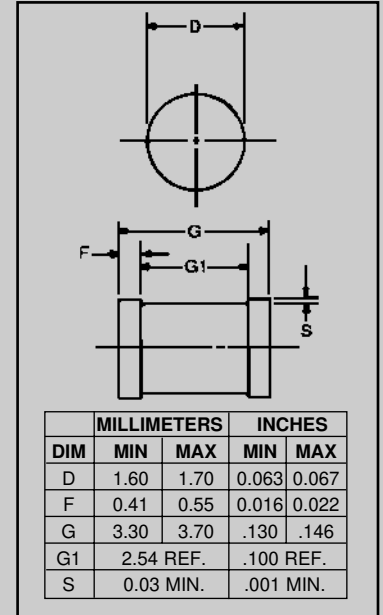


FIGURE 1

DESIGN DATA

CASE: DO-213AA, Hermetically sealed glass case. (MELF, SOD-80, LL34)

LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: (R_{ΘJEC}):
100 °C/W maximum

THERMAL IMPEDANCE: (Z_{ΘJX}): 35
°C/W maximum

POLARITY: Cathode end is banded.

MOUNTING POSITION: Any.

MOUNTING SURFACE SELECTION:
The Axial Coefficient of Expansion (COE) Of this Device is Approximately +6PPM/°C. The COE of the Mounting Surface System Should Be Selected To Provide A Suitable Match With This Device.



CDLL483B, CDLL485B and CDLL486B

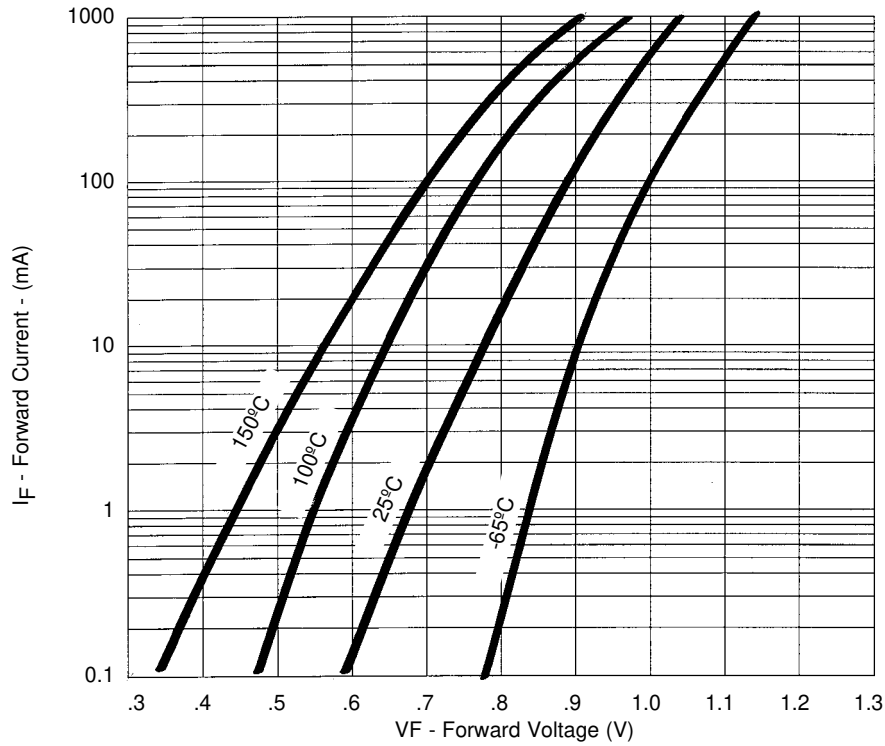
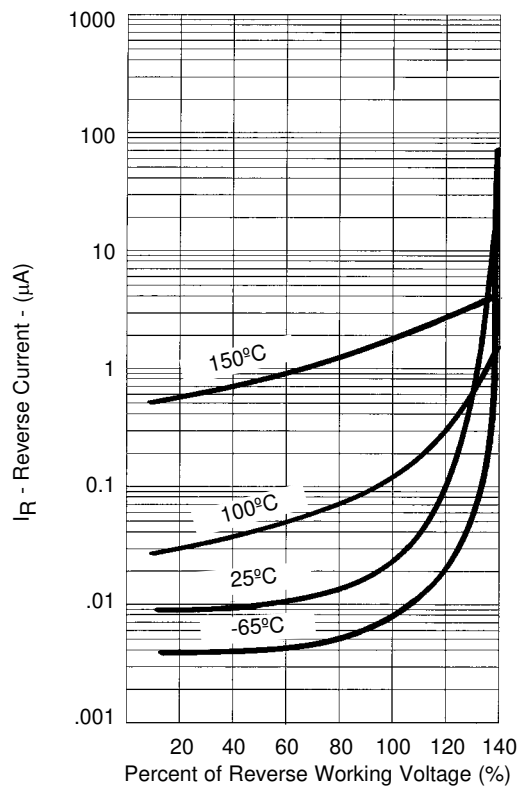


FIGURE 2
Typical Forward Current
vs Forward Voltage



NOTE : All temperatures shown on graphs are junction temperatures

FIGURE 3
Typical Reverse Current
vs Reverse Voltage